



April 2000

QFET™

FQP10N20

200V N-Channel MOSFET

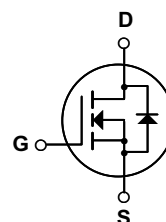
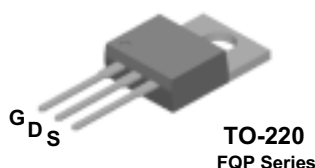
General Description

These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar stripe, DMOS technology.

This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency switching DC/DC converters, switch mode power supply, DC-AC converters for uninterrupted power supply, motor control.

Features

- 10A, 200V, $R_{DS(on)} = 0.36\Omega$ @ $V_{GS} = 10V$
- Low gate charge (typical 13.5 nC)
- Low C_{rss} (typical 13 pF)
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability



Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	FQP10N20	Units
V_{DSS}	Drain-Source Voltage	200	V
I_D	Drain Current - Continuous ($T_C = 25^\circ\text{C}$)	10	A
	- Continuous ($T_C = 100^\circ\text{C}$)	6.3	A
I_{DM}	Drain Current - Pulsed (Note 1)	40	A
V_{GSS}	Gate-Source Voltage	± 30	V
E_{AS}	Single Pulsed Avalanche Energy (Note 2)	180	mJ
I_{AR}	Avalanche Current (Note 1)	10	A
E_{AR}	Repetitive Avalanche Energy (Note 1)	8.7	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	5.5	V/ns
P_D	Power Dissipation ($T_C = 25^\circ\text{C}$)	87	W
	- Derate above 25°C	0.70	W/ $^\circ\text{C}$
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150	$^\circ\text{C}$
T_L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	300	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	Typ	Max	Units
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	--	1.44	$^\circ\text{C}/\text{W}$
$R_{\theta CS}$	Thermal Resistance, Case-to-Sink	0.5	--	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	--	62.5	$^\circ\text{C}/\text{W}$

Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	200	--	--	V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 250\text{ }\mu\text{A}$, Referenced to 25°C	--	0.19	--	$V/^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 200\text{ V}, V_{GS} = 0\text{ V}$	--	--	1	μA
		$V_{DS} = 160\text{ V}, T_C = 125^\circ\text{C}$	--	--	10	μA
I_{GSSF}	Gate-Body Leakage Current, Forward	$V_{GS} = 30\text{ V}, V_{DS} = 0\text{ V}$	--	--	100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	$V_{GS} = -30\text{ V}, V_{DS} = 0\text{ V}$	--	--	-100	nA

On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	3.0	--	5.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{ V}, I_D = 5\text{ A}$	--	0.28	0.36	Ω
g_{FS}	Forward Transconductance	$V_{DS} = 40\text{ V}, I_D = 5\text{ A}$ (Note 4)	--	6.7	--	S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$	--	510	670	pF
C_{oss}	Output Capacitance		--	95	130	pF
C_{rss}	Reverse Transfer Capacitance		--	13	17	pF

Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 100\text{ V}, I_D = 10\text{ A},$ $R_G = 25\text{ }\Omega$ (Note 4, 5)	--	13	40	ns
t_r	Turn-On Rise Time		--	90	190	ns
$t_{d(off)}$	Turn-Off Delay Time		--	26	70	ns
t_f	Turn-Off Fall Time		--	50	110	ns
Q_g	Total Gate Charge	$V_{DS} = 160\text{ V}, I_D = 10\text{ A},$ $V_{GS} = 10\text{ V}$ (Note 4, 5)	--	13.5	18	nC
Q_{gs}	Gate-Source Charge		--	3.8	--	nC
Q_{gd}	Gate-Drain Charge		--	5.5	--	nC

Drain-Source Diode Characteristics and Maximum Ratings

I _S	Maximum Continuous Drain-Source Diode Forward Current		--	--	10	A
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current		--	--	40	A
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = 10 A	--	--	1.5	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _S = 10 A, dI _F / dt = 100 A/μs (Note 4)	--	130	--	ns
Q _{rr}	Reverse Recovery Charge		--	0.6	--	μC

Notes:

1. Repetitive Rating : Pulse width limited by maximum junction temperature
2. $L = 2.7\text{ mH}, I_{AS} = 10\text{ A}, V_{DD} = 50\text{ V}, R_G = 25\text{ }\Omega$, Starting $T_J = 25^\circ\text{C}$
3. $I_{SD} \leq 10\text{ A}, di/dt \leq 300\text{ A}/\mu\text{s}, V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$
4. Pulse Test : Pulse width $\leq 300\mu\text{s}$, Duty cycle $\leq 2\%$
5. Essentially independent of operating temperature

Typical Characteristics

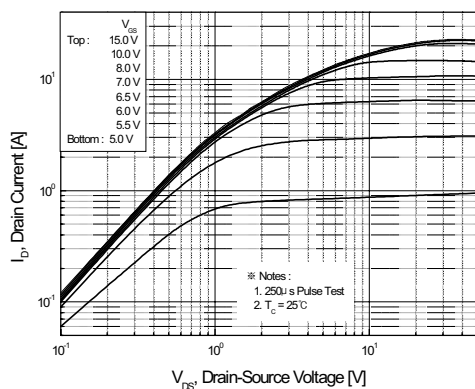


Figure 1. On-Region Characteristics

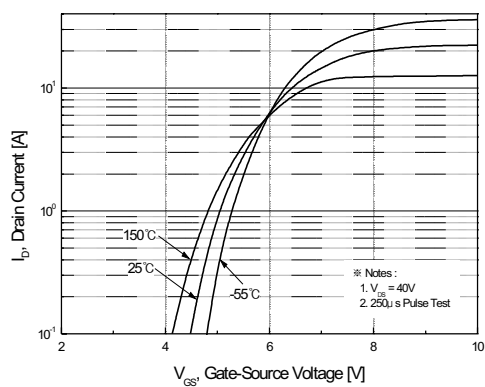


Figure 2. Transfer Characteristics

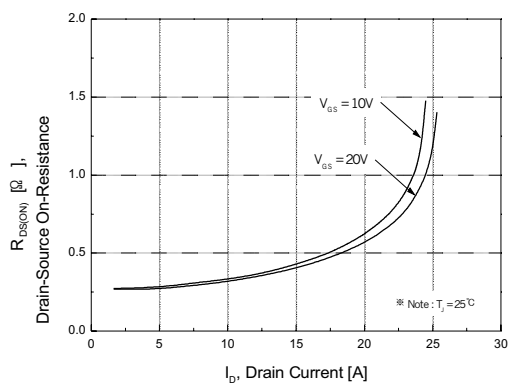


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

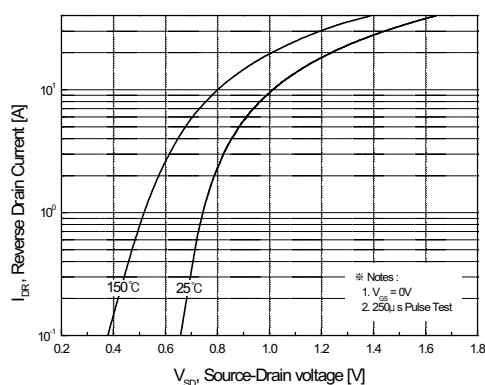


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

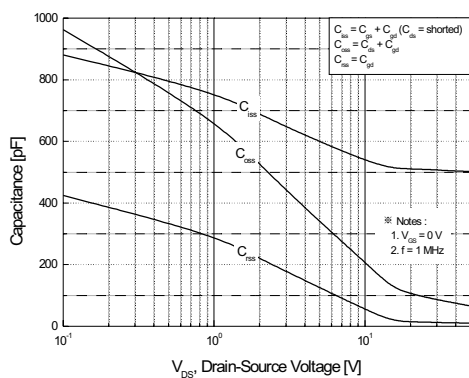


Figure 5. Capacitance Characteristics

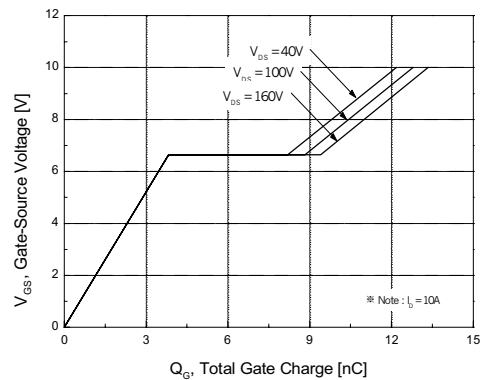


Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued)

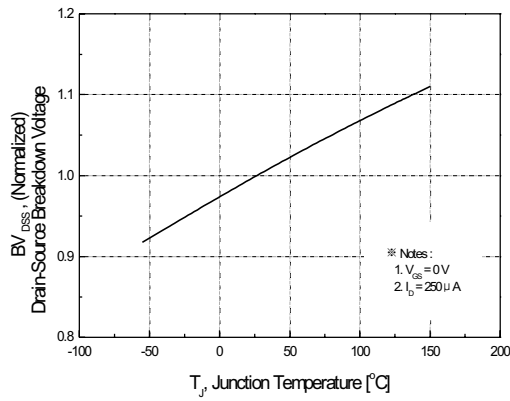


Figure 7. Breakdown Voltage Variation vs. Temperature

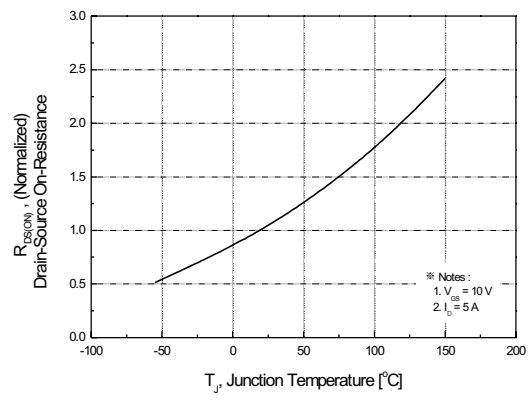


Figure 8. On-Resistance Variation vs. Temperature

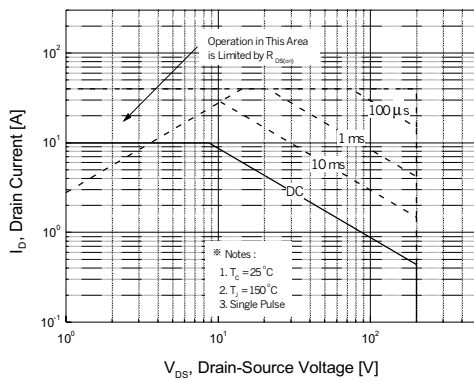


Figure 9. Maximum Safe Operating Area

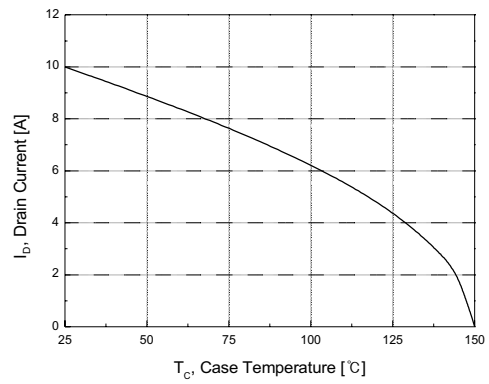


Figure 10. Maximum Drain Current vs. Case Temperature

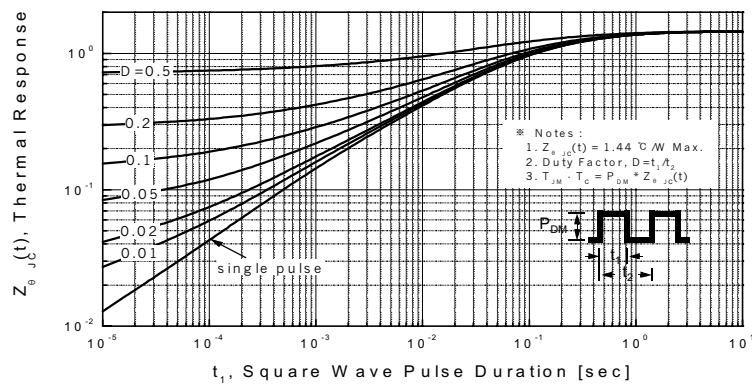
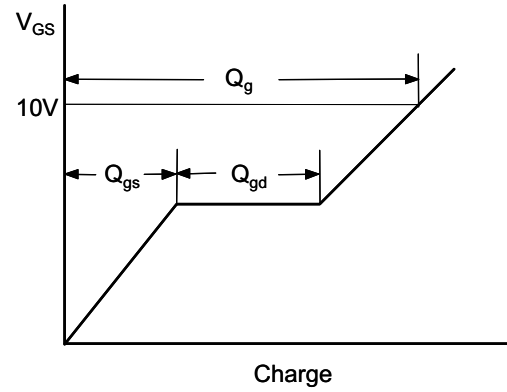
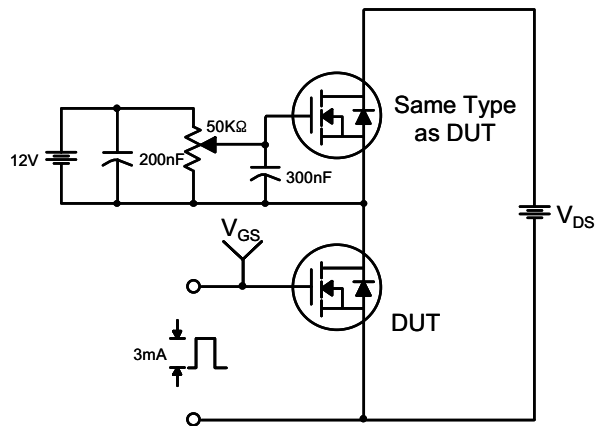
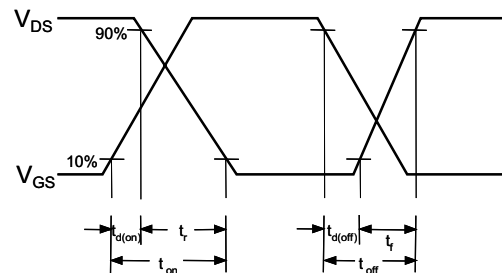
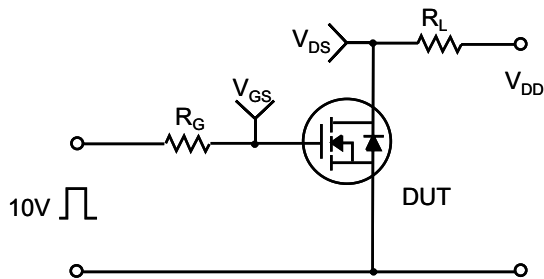


Figure 11. Transient Thermal Response Curve

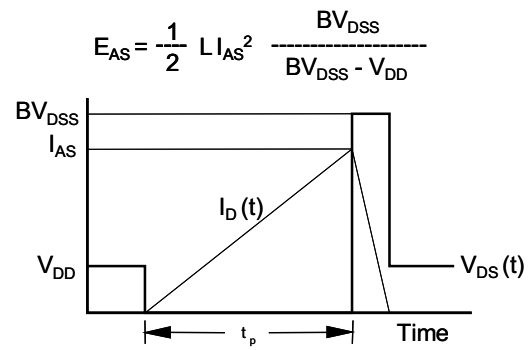
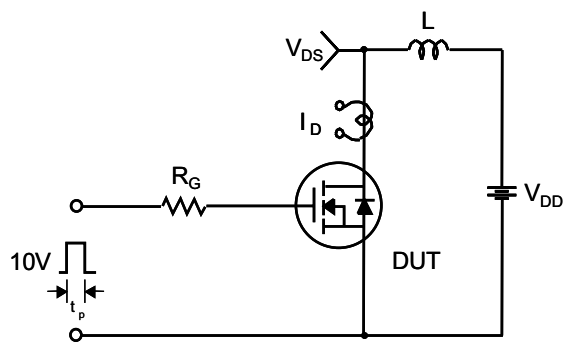
Gate Charge Test Circuit & Waveform



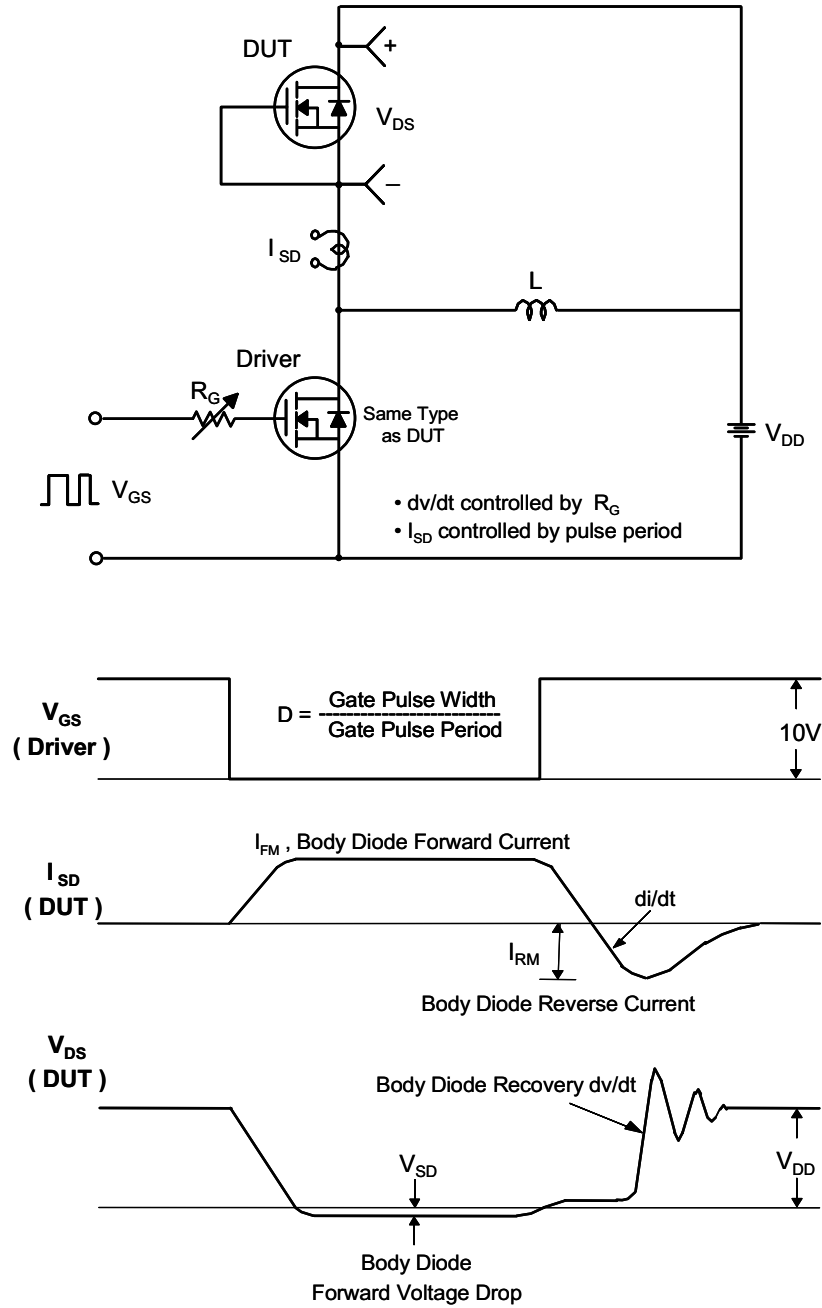
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching Test Circuit & Waveforms

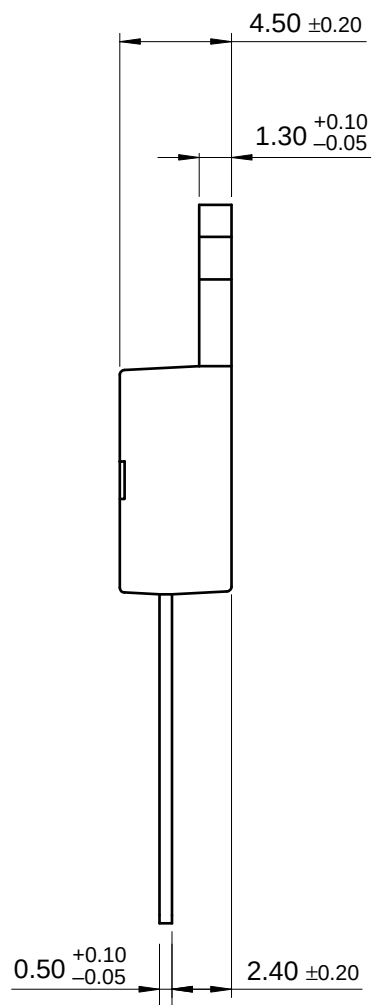


Peak Diode Recovery dv/dt Test Circuit & Waveforms



Package Dimensions

Technical drawing of a 3-pin connector. The drawing shows a top view and a side view. The top view dimensions are: overall width 9.90 ±0.20, distance from left edge to center pin 4.95 ±0.10, distance from center pin to right edge 4.95 ±0.10, distance from left edge to first pin 1.30 ±0.10, distance between pins 3.60 ±0.10, distance from center pin to right edge of housing 2.80 ±0.10, and overall height 18.95 MAX. The side view dimensions are: overall height 18.95 MAX, distance from top edge to first pin 13.08 ±0.20, distance between pins 1.27 ±0.10, distance from center pin to right edge of housing 1.52 ±0.10, and distance from top edge to top of housing 15.90 ±0.20. The drawing also shows a 45° chamfer on the pins and a 0.80 ±0.10 dimension for the pin thickness. The drawing is labeled with dimensions in millimeters (mm) and includes tolerances.



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result in significant injury to the user.

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